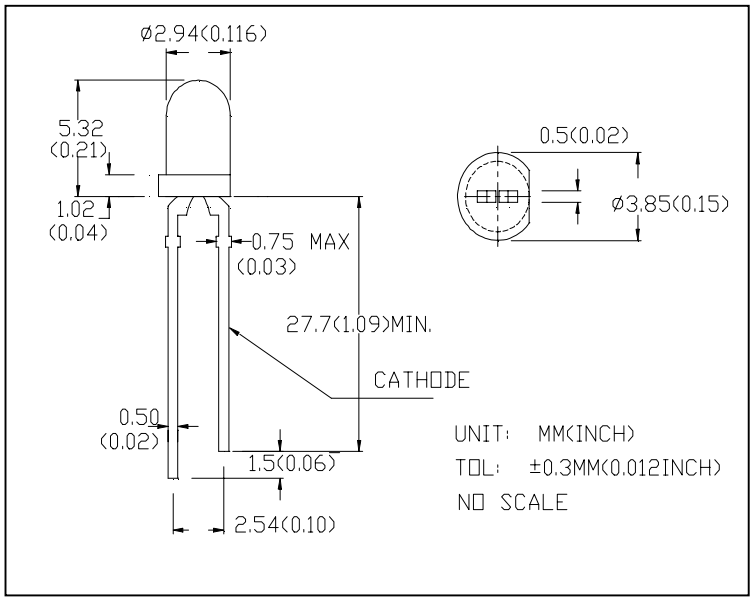
MICRO ELECTRONICS

MWB32WA-DI

ULTRA HIGH BRIGHTNESS WHITE LED LAMP

DESCRIPTION

MWB32WA-DI is an ultra high brightness InGaN/GaN white LED lamp encapsulated in a 3mm diameter white diffused lens .



ABSOLUTE MAXIMUM RATINGS

Power Dissipation @ Ta=25°C	100mW
Forward Current, DC (IF)	30mA
Reverse Voltage	5V
Operating Temperature Range	-20 to +80°C
Storage Temperature Range	-30 to +100°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Forward Voltage	VF		3.5	4.5	V	IF=20mA
Reverse Breakdown Voltage	BVR	5			V	IR=100µA
Viewing Angle	2θ 1/2		50		degree	IF=20mA
Luminous Intensity	IV	500	1500		mcd	IF=20mA
Chromaticity Coordinates	x	0.22	0.34	0.42		IF=20mA
	y	0.22	0.34	0.42		IF=20mA

CAUTION

Static eletricity and surge damages the LED ,It is recommended to use a wrist band or anti-eletrostatic glove when handling the LED . All devices,equipment and machinery must be properly grou

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SPECIFICATIONS FOR BIN GRADING

MWB32WA-DI-X X

Chromaticity Coordinates

Luminous Intensity

PARAMETER	BIN	SYMBOL	MIN	TYP		MAX	UNIT	CONDITIONS
Luminous Intensity	1	IV	500	—		1000	mcd	IF=20mA
	2	IV	1000	—		1500		
	3	IV	1500	—		—		
Chromaticity Coordinates	A	x	0.220	0.220	0.270	0.270	TOL: ±0.02	IF=20mA
		y	0.220	0.363	0.377	0.234		
	B	x	0.270	0.270	0.320	0.320		
		y	0.234	0.377	0.392	0.249		
	C	x	0.320	0.320	0.370	0.370		
		y	0.249	0.392	0.406	0.263		
	D	x	0.370	0.370	0.420	0.420		
		y	0.263	0.406	0.420	0.277		

CIE CHROMATICITY DIAGRAM